

## AMENDMENTS

### In the Claims:

This listing of claims replaces all prior versions, and listings, of claims in this application.

1. (Currently Amended) A semiconductor laser device comprising, on an n-type GaAs substrate, at least an n-type lower cladding layer, a lower guide layer, an InGaAsP quantum well active layer composed of one or a plurality of well layers and a plurality of barrier layers alternately disposed, an upper guide layer, a p-type upper cladding layer and a current blocking layer,

wherein the quantum well active layer is stacked so that an n-side barrier layer is present on a side of the lower guide layer and a p-side barrier layer is present on a side of the upper guide layer,

wherein the p-side barrier layer has a smaller thickness than a thickness of the n-side barrier layer,

wherein said semiconductor laser device has an oscillation wavelength of more than 760 nm and less than 800 nm, and the n-side barrier layer has a thickness of 70 Å or more, and

wherein the current blocking layer consists of a solid layer.

2. (Canceled)

3. (Original) The semiconductor laser device according to claim 1, wherein the p-side barrier layer has a thickness of less than 70 Å.

4. (Currently Amended) A semiconductor laser device comprising, on a p-type GaAs substrate, at least a p-type lower cladding layer, a lower guide layer, an InGaAsP quantum well active layer composed of one or a plurality of well layers and a plurality of barrier layers alternately disposed, an upper guide layer, an n-type upper cladding layer and a current blocking layer,

wherein the quantum well active layer is stacked so that a p-side barrier layer is present on a side of the lower guide layer and an n-side barrier layer is present on a side of the upper guide layer,

wherein the p-side barrier layer has a smaller thickness than a thickness of the n-side barrier layer,

wherein said semiconductor laser device has an oscillation wavelength of more than 760 nm and less than 800 nm, and the n-side barrier layer has a thickness of 70 Å or more, and

wherein the current blocking layer consists of a solid layer.

5. (Canceled)

6. (Original) The semiconductor laser device according to claim 4, wherein the p-side barrier layer has a thickness of less than 70 Å.

7. (Original) The semiconductor laser device according to claim 1, wherein the upper guide layer and the lower guide layer are formed of AlGaAs.

8. (Original) The semiconductor laser device according to claim 4, wherein the upper guide layer and the lower guide layer are formed of AlGaAs.

9. (Original) The semiconductor laser device according to claim 7, wherein an Al mole fraction of the upper guide layer and the lower guide layer is more than 0.2.

10. (Original) The semiconductor laser device according to claim 8, wherein an Al mole fraction of the upper guide layer and the lower guide layer is more than 0.2.

11. (Original) The semiconductor laser device according to claim 1, wherein the well layer(s) has a compressive strain.

12. (Original) The semiconductor laser device according to claim 4, wherein the well layer(s) has a compressive strain.

13. (Original) The semiconductor laser device according to claim 11, wherein a quantity of an absolute value of the compressive strain is not more than 3.5%.

14. (Original) The semiconductor laser device according to claim 12, wherein a quantity of an absolute value of the compressive strain is not more than 3.5%.

15. (Original) The semiconductor laser device according to claim 1, wherein the barrier layers have a tensile strain.

16. (Original) The semiconductor laser device according to claim 4, wherein the barrier layers have a tensile strain.

17. (Original) The semiconductor laser device according to claim 15, wherein a quantity of the tensile strain is not more than 3.5%.

18. (Original) The semiconductor laser device according to claim 16, wherein a quantity of the tensile strain is not more than 3.5%.

19. (Original) An optical disc unit wherein the semiconductor laser device of claim 1 is used.